

PROCESS FOR FABRICATING THIN FILM TRANSISTORS2 Abstract of the Disclosure

3 Transistors are formed by depositing at least one layer of
4 semiconductor material on a substrate comprising a polyphenylene polyimide. The
5 substrate permits the use of processing temperatures in excess of 300°C during the
6 processes used to form the transistors, thus allowing the formation of high quality
7 silicon semiconductor layers. The substrate also has a low coefficient of thermal
8 expansion, which closely matches that of silicon, thus reducing any tendency for a
9 silicon layer to crack or delaminate.